Atty. Docket 101453-00094

Response to Office Action dated 08/25/2004

II. Amendments to the Claims

1. (Currently Amended) A method of continuously depositing a coating on a substrate

comprising

loading the substrate onto a feed spool external to a vacuum deposition chamber;

reducing the pressure in the deposition chamber to no greater than about 10⁻⁵ Torr;

feeding the substrate from the feed spool through the deposition chamber containing at

least one deposition zone;

helically winding the substrate around a stationary cooling block of non-circular cross

section such that the substrate traverses the at least one deposition zone multiple times wherein

multiple layers of a coating are applied to the substrate and for a total period of time sufficient to

deposit a coating of the desired thickness onto the substrate; and

loading the coated substrate onto a take-up spool.

2. (Original) The method of claim 1 where the cooling block cools the substrate by conductive

and convective cooling.

2

Atty. Docket 101453-00094

Response to Office Action dated 08/25/2004

3. (Original) The method of claim 1 where there the substrate is a metal substrate and the coating is a biaxially-textured buffer layer for a high temperature superconducting material.

4. (Original) The method of claim 1 where the vacuum deposition chamber comprises one deposition zone and one coating modification zone.

5. (Original) The method of claim 2 where the length of the deposition zone is controlled by a movable shutter.

6. (Original) The method of claim 1 where the deposition chamber comprises two deposition zones and the substrate alternately traverses each deposition zone at least twice.

7. (Original) The method of claim 6 where a different coating is deposited in each deposition zone.

8. (Original) The method of claim 6 where the same coating is deposited in each deposition zone.

9. (Currently Amended) A method of continuously depositing a coating on a substrate comprising

loading the substrate onto a feed spool external to a first vacuum deposition chamber; reducing the pressure in the first deposition chamber to no greater than about 10⁻⁵ Torr;

Atty. Docket 101453-00094

Response to Office Action dated 08/25/2004

feeding the substrate from the feed spool through the first deposition chamber containing at least one deposition zone;

helically winding the substrate around a <u>stationary</u> cooling block <u>of non-circular cross</u>

<u>section</u> in the first deposition chamber such that the substrate traverses the at least one deposition

zone multiple times wherein multiple layers of a coating are applied to the substrate and for a

total period of time sufficient to deposit a coating of the desired thickness onto the substrate; and

feeding the coated tape exiting the first deposition chamber to a second deposition chamber, which is dynamically isolated from the first deposition chamber.

10. (Original) The method of claim 9 where the substrate resides in the deposition zone of the first deposition chamber for a period of time different than the time it resides in the deposition zone of the second deposition chamber.

11. (Original) The method of claim 9 where the two deposition chambers are connected via a Tee-tube.

- 12. (Original) The method of claim 11 where the Tee tube is between 6 and 12 inches long and has a diameter just sufficient to accommodate the substrate.
- 13. (Original) The method of claim 9 where the second deposition chamber contains a sputtering deposition zone where a coating is applied to the substrate by a sputtering process.

Atty. Docket 101453-00094

Response to Office Action dated 08/25/2004

14. (Original) The method of claim 13 where the length of the sputtering deposition zone is controlled by a variable shutter.

15. (Original) The method of claim 13 where the sputtering process utilizes an RF magnetron.

16. (Currently Amended) A method of continuously coating a substrate with a buffer layer as a support for a ceramic superconducting material comprising

providing a feed spool of substrate;

threading the substrate into a vacuum deposition chamber;

loading at least one coating material that is to be coated onto the surface of the substrate into the vacuum deposition chamber;

reducing the pressure in the deposition chamber to no greater than about 10⁻⁵ Torr, injecting oxygen into the deposition chamber;

initializing an energy source located in the deposition chamber to a pre-determined power level and trajectory;

vaporizing the coating material by bombarding the coating material with electrons or ions produced by the energy source;

feeding the substrate through a deposition zone in the vacuum chamber;

allowing the coating vaporized material to impinge upon the surface of the substrate in the deposition zone;

Atty. Docket 101453-00094

Response to Office Action dated 08/25/2004

wrapping the substrate exiting the deposition zone helically around a <u>stationary</u> cooling block <u>of non-circular cross section</u> such that the substrate traverses the deposition zone multiple times allowing the vaporized coating material to impinge upon the surface of the substrate for a period of time sufficient to deposit a coating onto the substrate; and

collecting the coated substrate on a take-up spool.

17. (Original) The method of claim 16 where the feed and take up spools are located external to the deposition chamber.

18. (Currently Amended) A method of continuously coating a substrate with a buffer layer as a support for a ceramic superconducting material comprising

providing a feed spool of substrate;

threading the substrate into a vacuum deposition chamber;

loading at least one coating material that is to be coated onto the surface of the substrate into the vacuum deposition chamber;

reducing the pressure in the deposition chamber to no greater than about 10⁻⁵ Torr,

injecting oxygen into the deposition chamber;

initializing an energy source located in the deposition chamber to a pre-determined power level and trajectory;

Atty. Docket 101453-00094

Response to Office Action dated 08/25/2004

vaporizing the coating material by bombarding the coating material with electrons or ions produced by the energy source;

feeding the substrate through a deposition zone in the vacuum chamber;

allowing the coating vaporized material to impinge upon the surface of the substrate in the deposition zone;

wrapping the substrate exiting the deposition zone helically around a <u>stationary</u> cooling block <u>of non-circular cross section</u> such that the substrate traverses the deposition zone multiple times allowing the vaporized coating material to impinge upon the surface of the substrate for a period of time sufficient to deposit a coating onto the substrate; and

feeding the coated substrate exiting the first deposition chamber to a second vacuum deposition chamber, which is dynamically isolated from the first deposition chamber.

- 19. (Original) The method of claim 18 where the coated tape exiting the deposition chamber is fed to a second deposition chamber via a Tee-tube.
- 20. (Original) The method of claim 18 where the tee tube is between 6 and 12 inches long and has a diameter just sufficient to accommodate the substrate.
- 21. (Original) The method of claim 18 where the substrate resides in the deposition zone of the first deposition chamber for a period of time different than the time it resides in the deposition zone of the second deposition chamber.

Atty. Docket 101453-00094

Response to Office Action dated 08/25/2004

- 22. (Original) The method of claim 18 where the first vacuum deposition chamber comprises one deposition zone and also comprises a coating modification zone.
- 23. (Original) The method of claim 18 where there the substrate is a metal substrate and the coating is an epitaxially deposited buffer layer for a high temperature superconducting material
- 24. (Original) The method of claim 18 where the second deposition chamber contains a deposition zone where a coating is applied to the substrate by a sputtering process.
- 25. (Original) The method of claim 24 where the length of the sputtering deposition zone is controlled by a variable shutter.
- 26. (Original) The method of claim 24 where the sputtering process utilizes an RF magnetron.
- **27.** (Original) The method of claim 18 where the first deposition chamber comprises two physically separate deposition zones and where the substrate alternately traverses each deposition zone.
- **28.** (Original) The method of claim 27 where a different coating is deposited in each deposition zone.
- 29. (Original) The method of claim 27 where the same coating is deposited in each deposition zone.

Atty. Docket 101453-00094

Response to Office Action dated 08/25/2004

30. (Original) The method of claim 27 where a different coating is applied in each of the deposition zones.

31. (Original) The method of claim 27 where a different process is used in each of the deposition zones.

32. (Currently Amended) A method of continuously coating a substrate with a buffer layer as a support for a ceramic superconducting material comprising

loading the substrate onto a feed spool,

feeding the substrate through an vacuum deposition chamber wherein a layer of a coating is applied to the substrate in a deposition zone and the coating is modified by treatment in a coating modification zone where the substrate is helically wound around a <u>stationary</u> cooling block <u>of non-circular cross section</u> and the deposition zone and coating modification zone are located on opposite sides of the cooling block and

loading the coated substrate onto a take-up spool.